

Amendments to the Specification:

Please replace the paragraph beginning on page 7, line 17, with the following rewritten paragraph:

Shown in FIG.6 is the detailed layer structure of EL53 (subpixel 600) in pixel 500. EL53 is the same as EL33 except that an intermediate connector 534 is sandwiched between the 2nd ETL of EL unit 133 and the 1st HTL of EL unit 335. This is another type of vertically stacked structures. Tanaka et al. in U.S. Patent No. 6,107,734, Jones et al. in U.S. Patent No. 6,337,492, Kido et al. in Japanese Patent Application JP200304676A, and Liao et al. in ~~Docket~~ US Patent No. 6,717,358 have disclosed the methods to fabricate this structure. The disclosures of the cited patents and patent applications are incorporated herein by reference.

Please replace the paragraph beginning on page 15, line 5, with the following rewritten paragraph:

The intermediate connector 534 includes at least one inorganic semiconducting material or combinations of more than one of the semiconducting materials. Suitable semiconducting materials should have an optical energy band gap less than 4.0 eV. The optical energy band gap is defined as the onset energy of the optical absorption peak. The optical energy band gap can be measured using a UV-Vis absorption spectrometer (such as an HP 8453 UV-Vis Spectrometer). A useful class of materials can be chosen from the compounds of subpixels listed in groups IVA, VA, VIA, VIIA, VIIIA, IB, IIB, IIIB, IVB, and VB in the Periodic Table of the Elements (e.g. the Periodic Table of the Elements published by VWR Scientific Products). These compounds include the carbides, silicides, nitrides, phosphides, arsenides, oxides, sulfides, selenides, tellurides, or mixture thereof. These semiconducting compounds can be in either ~~stoichiometric~~ stoichiometric or ~~non-stoichiometric~~ non-stoichiometric states, that is they may contain excess or deficit metal component. Particularly useful materials for the intermediate connector 534 are the semiconducting oxides of titanium, zirconium, hafnium, vanadium, niobium, tantalum, chromium, molybdenum, tungsten, manganese, rhenium, iron, ruthenium, osmium, cobalt, rhodium, iridium, nickel, palladium, platinum, copper, zinc, cadmium, gallium, thallium, silicon,

germanium, lead, antimony, or combinations thereof. Particularly useful materials for the intermediate connector 534 also including zinc selenide, gallium nitride, silicon carbide, or combinations thereof. Preferably useful materials for the intermediate connector 534 include WO_3 , MoO_3 , In_2O_3 , SnO_2 , PbO , Sb_2O_3 , SnSe , SnS , ZnSe , ZnS , VO_2 , or V_2O_5 .